

Amendments to the Specification:

Please amend paragraph [0004] as follows:

A second aspect of the present invention is a method of fabricating a dual damascene ~~method~~ structure, comprising: forming a first interconnect level comprising a first dielectric layer and including a multiplicity of first damascene or dual damascene conductive wires, each first damascene or dual damascene conductive wire extending from a top surface of the first dielectric layer a distance toward a bottom surface of the first dielectric layer, the distance less than a thickness of the first dielectric layer; forming a second interconnect level directly above and in contact with the first dielectric layer, the second interconnect level comprising a second dielectric layer and including a multiplicity of second dual damascene conductive wires, each second dual damascene conductive wire extending from a top surface of the second dielectric layer a distance toward a bottom surface of the second dielectric layer, the distance less than a thickness of the second dielectric layer; and forming a dual damascene conductive via bar within the second interconnect level and integral with and extending from a bottom surface of one of the multiplicity of the second dual damascene conductive wires and a top surface of one of the multiplicity of the first dual damascene conductive wires, the dual damascene conductive via bar having a length greater than its width, the length and width of the dual damascene conductive via bar extending in the plane defined by the top surface of the second dielectric layer.